

In-Man Kang

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138
papers

1,042
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164
ext. papers

1,337
ext. citations

2.2
avg, IF

4.4
L-index

#	Paper	IF	Citations
138	. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 1388-1396	2.9	124
137	The analysis of dark signals in the CMOS APS imagers from the characterization of test structures. <i>IEEE Transactions on Electron Devices</i> , 2004 , 51, 178-184	2.9	84
136	. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 4164-4171	2.9	65
135	Non-quasi-static small-signal modeling and analytical parameter extraction of SOI FinFETs. <i>IEEE Nanotechnology Magazine</i> , 2006 , 5, 205-210	2.6	63
134	AlGaN/GaN FinFET With Extremely Broad Transconductance by Side-Wall Wet Etch. <i>IEEE Electron Device Letters</i> , 2015 , 36, 1008-1010	4.4	45
133	Simulation study on effect of drain underlap in gate-all-around tunneling field-effect transistors. <i>Current Applied Physics</i> , 2013 , 13, 1143-1149	2.6	32
132	Silicon-compatible compound semiconductor tunneling field-effect transistor for high performance and low standby power operation. <i>Applied Physics Letters</i> , 2011 , 99, 243505	3.4	30
131	. <i>IEEE Electron Device Letters</i> , 2016 , 37, 855-858	4.4	25
130	Suppression of current collapse in AlGaN/GaN MISHFET with carbon-doped GaN/undoped GaN multi-layered buffer structure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 1116-1121	1.6	24
129	Five-Step (Pad Pad Short Pad Open Short Open) De-Embedding Method and Its Verification. <i>IEEE Electron Device Letters</i> , 2009 , 30, 398-400	4.4	24
128	Separate Extraction of Gate Resistance Components in RF MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 1459-1463	2.9	21
127	Design and analysis of Si-based arch-shaped gate-all-around (GAA) tunneling field-effect transistor (TFET). <i>Current Applied Physics</i> , 2015 , 15, 208-212	2.6	19
126	Low voltage operation of GaN vertical nanowire MOSFET. <i>Solid-State Electronics</i> , 2018 , 145, 1-7	1.7	19
125	Design optimization of tunneling field-effect transistor based on silicon nanowire PNP structure and its radio frequency characteristics. <i>Current Applied Physics</i> , 2012 , 12, 673-677	2.6	18
124	1/f-Noise in AlGaN/GaN Nanowire Omega-FinFETs. <i>IEEE Electron Device Letters</i> , 2017 , 38, 252-254	4.4	17
123	Effects of sidewall MOS channel on performance of AlGaN/GaN FinFET. <i>Microelectronic Engineering</i> , 2015 , 147, 155-158	2.5	17
122	Fabrication and Characterization of a Thin-Body Poly-Si 1T DRAM With Charge-Trap Effect. <i>IEEE Electron Device Letters</i> , 2019 , 40, 566-569	4.4	15

121	Sol-Gel Processed Yttrium-Doped SnO ₂ Thin Film Transistors. <i>Electronics (Switzerland)</i> , 2020 , 9, 254	2.6	12
120	TMAH-based wet surface pre-treatment for reduction of leakage current in AlGa _N /Ga _N MIS-HEMTs. <i>Solid-State Electronics</i> , 2016 , 124, 54-57	1.7	12
119	. <i>IEEE Electron Device Letters</i> , 2009 , 30, 404-406	4.4	11
118	The Crucial Role of Quaternary Mixtures of Active Layer in Organic Indoor Solar Cells. <i>Energies</i> , 2019 , 12, 1838	3.1	10
117	A polycrystalline-silicon dual-gate MOSFET-based 1T-DRAM using grain boundary-induced variable resistance. <i>Applied Physics Letters</i> , 2019 , 114, 183503	3.4	10
116	First demonstration of GaN-based vertical nanowire FET with top-down approach 2015 ,		9
115	Effect of Mg Doping on the Electrical Performance of a Sol-Gel-Processed SnO ₂ Thin-Film Transistor. <i>Electronics (Switzerland)</i> , 2020 , 9, 523	2.6	9
114	Effect of Annealing Ambient on SnO ₂ Thin Film Transistors Fabricated via An Ethanol-based Sol-gel Route. <i>Electronics (Switzerland)</i> , 2019 , 8, 955	2.6	9
113	Radio Frequency Performance of Hetero-Gate-Dielectric Tunneling Field-Effect Transistors. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 124301	1.4	9
112	Deep Sub-60 mV/decade Subthreshold Swing in AlGa _N /Ga _N FinMISHFETs with M-Plane Sidewall Channel. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1699-1703	2.9	8
111	More Accurate and Reliable Extraction of Tunneling Resistance in Tunneling FET and Verification in Small-Signal Circuit Operation. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 3318-3324	2.9	8
110	InGaAs/InP heterojunction-channel tunneling field-effect transistor for ultra-low operating and standby power application below supply voltage of 0.5V. <i>Current Applied Physics</i> , 2013 , 13, 2051-2054	2.6	8
109	A New Noise Parameter Model of Short-Channel MOSFETs. <i>Radio Frequency Integrated Circuits (RFIC) Symposium, IEEE</i> , 2007 ,		8
108	Fully Coupled Finite-Element Analysis for Surface Discharge on Solid Insulation in Dielectric Liquid With Experimental Validation. <i>IEEE Transactions on Magnetics</i> , 2016 , 52, 1-4	2	7
107	Numerical Analysis on Effective Mass and Traps Density Dependence of Electrical Characteristics of a-IGZO Thin-Film Transistors. <i>Electronics (Switzerland)</i> , 2020 , 9, 119	2.6	7
106	Capacitorless one-transistor dynamic random-access memory based on asymmetric double-gate Ge/GaAs-heterojunction tunneling field-effect transistor with n-doped boosting layer and drain-underlap structure. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 04FG03	1.4	7
105	GaN junctionless trigate field-effect transistor with deep-submicron gate length: Characterization and modeling in RF regime. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 118001	1.4	7
104	Mixed-Mode Simulation of Nanowire Ge/GaAs Heterojunction Tunneling Field-Effect Transistor for Circuit Applications. <i>IEEE Journal of the Electron Devices Society</i> , 2013 , 1, 48-53	2.3	7

103	RF Model of BEOL Vertical Natural Capacitor (VNCAP) Fabricated by 45-nm RF CMOS Technology and Its Verification. <i>IEEE Electron Device Letters</i> , 2009 , 30, 538-540	4.4	7
102	Extraction of π -Type Substrate Resistance Based on Three-Port Measurement and the Model Verification up to 110 GHz. <i>IEEE Electron Device Letters</i> , 2007 , 28, 425-427	4.4	7
101	Contact line curvature-induced molecular misorientation of a surface energy patterned organic semiconductor in meniscus-guided coating. <i>Applied Surface Science</i> , 2020 , 504, 144362	6.7	7
100	Extremely bias stress stable enhancement mode sol-gel-processed SnO ₂ thin-film transistors with Y ₂ O ₃ passivation layers. <i>Applied Surface Science</i> , 2021 , 559, 149971	6.7	7
99	Fabrication of AlGa _N /Ga _N MISHEMT with dual-metal gate electrode and its performances. <i>Applied Physics A: Materials Science and Processing</i> , 2020 , 126, 1	2.6	6
98	Silicon-compatible high-hole-mobility transistor with an undoped germanium channel for low-power application. <i>Applied Physics Letters</i> , 2013 , 103, 222102	3.4	6
97	Normally-off AlGa _N /Ga _N -based MOS-HEMT with self-terminating TMAH wet recess etching. <i>Solid-State Electronics</i> , 2018 , 141, 7-12	1.7	6
96	Fluoropolymer-based organic memristor with multifunctionality for flexible neural network system. <i>Npj Flexible Electronics</i> , 2021 , 5,	10.7	6
95	Short-Channel Tunneling Field-Effect Transistor with Drain-Overlap and Dual-Metal Gate Structure for Low-Power and High-Speed Operations. <i>Journal of Nanoscience and Nanotechnology</i> , 2015 , 15, 7430-5 ¹⁻³	5.3	5
94	Enhancement Mode Flexible SnO ₂ Thin Film Transistors Via a UV/Ozone-Assisted Sol-Gel Approach. <i>IEEE Access</i> , 2020 , 8, 123013-123018	3.5	5
93	Analysis of the Sensing Margin of Silicon and Poly-Si 1T-DRAM. <i>Micromachines</i> , 2020 , 11,	3.3	5
92	Application of Genetic Algorithm for More Efficient Multi-Layer Thickness Optimization in Solar Cells. <i>Energies</i> , 2020 , 13, 1726	3.1	5
91	Highly sensitive ion sensor based on the MOSFETBJT hybrid mode of a gated lateral BJT. <i>Sensors and Actuators B: Chemical</i> , 2013 , 181, 44-49	8.5	5
90	Non-Quasi-Static Modeling of Silicon Nanowire MetalOxideSemiconductor Field-Effect Transistor and Its Model Verification up to 1 THz. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 110206	1.4	5
89	2.4 GHz ISM-Band Receiver Design in a 0.18 μm Mixed Signal CMOS Process. <i>IEEE Microwave and Wireless Components Letters</i> , 2007 , 17, 736-738	2.6	5
88	Improved negative bias stability of sol-gel processed Ti-doped SnO ₂ thin-film transistors. <i>Semiconductor Science and Technology</i> , 2020 , 35, 115023	1.8	5
87	Control of silver nanowire-elastomer nanocomposite networks through elaborate direct printing for ultrathin and stretchable strain sensors. <i>Composites Science and Technology</i> , 2020 , 200, 108471	8.6	5
86	Design and Optimization of Germanium-Based Gate-Metal-Core Vertical Nanowire Tunnel FET. <i>Micromachines</i> , 2019 , 10,	3.3	5

85	Control of transconductance in high performance AlGaIn/GaN FinFETs 2015 ,		4
84	Effects of Contact Potential and Sidewall Surface Plane on the Performance of GaN Vertical Nanowire MOSFETs for Low-Voltage Operation. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 1547-1552	2.9	4
83	Analysis of operation characteristics of junctionless poly-Si 1T-DRAM in accumulation mode. <i>Semiconductor Science and Technology</i> , 2019 , 34, 105007	1.8	4
82	Importance of Blade-Coating Temperature for Diketopyrrolopyrrole-based Thin-Film Transistors. <i>Crystals</i> , 2019 , 9, 346	2.3	4
81	Performance enhancement of AlGaIn/GaN nanochannel omega-FinFET. <i>Solid-State Electronics</i> , 2017 , 129, 196-199	1.7	4
80	Performance of Gate-All-Around Tunneling Field-Effect Transistors Based on Si _{1-x} Gex Layer. <i>IEICE Transactions on Electronics</i> , 2012 , E95.C, 814-819	0.4	4
79	Electrical Characteristics of Enhancement-Mode n-Channel Vertical GaN MOSFETs and the Effects of Sidewall Slope. <i>Journal of Electrical Engineering and Technology</i> , 2015 , 10, 1131-1137	1.4	4
78	Fabrication of AlGaIn/GaN Fin-Type HEMT Using a Novel T-Gate Process for Improved Radio-Frequency Performance. <i>IEEE Access</i> , 2020 , 8, 139156-139160	3.5	4
77	Design optimization of vertical nanowire tunneling field-effect transistor based on AlGaSb/InGaAs heterojunction layer. <i>Current Applied Physics</i> , 2016 , 16, 681-685	2.6	4
76	Capacitorless One-Transistor Dynamic Random-Access Memory Based on Double-Gate Metal-Oxide-Semiconductor Field-Effect Transistor with Si/SiGe Heterojunction and Underlap Structure for Improvement of Sensing Margin and Retention Time. <i>Journal of Nanoscience and Nanotechnology</i> , 2019 , 19, 6023-6030	1.3	3
75	A Novel Analysis of $\{L\}_{\text{gd}}$ Dependent-1/ $\{f\}$ Noise in In _{0.08} Al _{0.92} N/GaN. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1552-1555	4.4	3
74	Heteromaterial gate tunneling field-effect transistor for high-speed and radio-frequency applications. <i>Journal of Nanoscience and Nanotechnology</i> , 2014 , 14, 8136-40	1.3	3
73	Fabrication of high performance AlGaIn/GaN FinFET by utilizing anisotropic wet etching in TMAH solution 2015 ,		3
72	Design optimization of vertical double-gate tunneling field-effect transistors. <i>Journal of the Korean Physical Society</i> , 2012 , 61, 1679-1682	0.6	3
71	Compound Semiconductor Tunneling Field-Effect Transistor Based on Ge/GaAs Heterojunction with Tunneling-Boost Layer for High-Performance Operation. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 04CC04	1.4	3
70	Simulation for silicon-compatible InGaAs-based junctionless field-effect transistor using InP buffer layer. <i>Semiconductor Science and Technology</i> , 2013 , 28, 105007	1.8	3
69	Investigation of source-to-drain capacitance by DIBL effect of silicon nanowire MOSFETs. <i>IEICE Electronics Express</i> , 2010 , 7, 1499-1503	0.5	3
68	Fabrication and Characterization of a GaN Light-emitting Diode (LED) with a Centered Island Cathode. <i>Journal of the Optical Society of Korea</i> , 2012 , 16, 349-353		3

67	Investigation of InAs/InGaAs/InP Heterojunction Tunneling Field-Effect Transistors. <i>Journal of Electrical Engineering and Technology</i> , 2014 , 9, 1654-1659	1.4	3
66	Polycrystalline silicon metal-oxide-semiconductor field-effect transistor-based stacked multi-layer one-transistor dynamic random-access memory with double-gate structure for the embedded systems. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SGGB01	1.4	3
65	Influence of Active Channel Layer Thickness on SnO ₂ Thin-Film Transistor Performance. <i>Electronics (Switzerland)</i> , 2021 , 10, 200	2.6	3
64	Single-event transient characteristics of vertical gate-all-around junctionless field-effect transistor on bulk substrate. <i>Applied Physics A: Materials Science and Processing</i> , 2021 , 127, 1	2.6	3
63	Design Optimization and Analysis of InGaAs/InAs/InGaAs Heterojunction-Based Electron Hole Bilayer Tunneling FETs. <i>Journal of Nanoscience and Nanotechnology</i> , 2019 , 19, 6070-6076	1.3	2
62	Effect of High-Speed Blade Coating on Electrical Characteristics in Polymer Based Transistors. <i>Journal of Nanoscience and Nanotechnology</i> , 2020 , 20, 5486-5490	1.3	2
61	Performance comparison between p ⁺⁺ and p ⁺ junction tunneling field-effect transistors. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 06HC01	1.4	2
60	Design Optimization of AlN/GaN-Based Double-Heterojunction Fin-Type High Electron Mobility Transistors for High On-State Current. <i>Journal of Nanoscience and Nanotechnology</i> , 2016 , 16, 10193-10198 ³	1.3	2
59	Design and Analysis of CMOS-Compatible III-V Compound Electron-Hole Bilayer Tunneling Field-Effect Transistor for Ultra-Low-Power Applications. <i>Journal of Nanoscience and Nanotechnology</i> , 2015 , 15, 7486-92	1.3	2
58	Analyses on RF Performances of Silicon-Compatible InGaAs-Based Planar-Type and Fin-Type Junctionless Field-Effect Transistors. <i>Journal of Nanoscience and Nanotechnology</i> , 2015 , 15, 7615-9	1.3	2
57	Design of a recessed-gate GaN-based MOSFET using a dual gate dielectric for high-power applications. <i>Journal of the Korean Physical Society</i> , 2014 , 65, 1579-1584	0.6	2
56	Improvement of Current Efficiency at High Field Regime Via Description of Roll-off Characteristic in Model Device of OLEDs. <i>Molecular Crystals and Liquid Crystals</i> , 2014 , 599, 79-85	0.5	2
55	Simulation study on scaling limit of silicon tunneling field-effect transistor under tunneling-predominance. <i>IEICE Electronics Express</i> , 2012 , 9, 828-833	0.5	2
54	Active and Passive RF Device Compact Modeling in CMOS Technoloies 2006 ,		2
53	Enhanced switching ratio of sputter-processed Y ₂ O ₃ RRAM device by suppressing oxygen-vacancy formation at high annealing temperature. <i>Semiconductor Science and Technology</i> ,	1.8	2
52	Design Optimization of Silicon-based Junctionless Fin-type Field-Effect Transistors for Low Standby Power Technology. <i>Journal of Electrical Engineering and Technology</i> , 2013 , 8, 1497-1502	1.4	2
51	Simulation of capacitorless dynamic random access memory based on junctionless FinFETs using grain boundary of polycrystalline silicon. <i>Applied Physics A: Materials Science and Processing</i> , 2020 , 126, 1	2.6	2
50	Gallium Nitride Normally Off MOSFET Using Dual-Metal-Gate Structure for the Improvement in Current Drivability. <i>Electronics (Switzerland)</i> , 2020 , 9, 1402	2.6	2

49	Design and Analysis of Gallium Nitride-Based p-i-n Diode Structure for Betavoltaic Cell with Enhanced Output Power Density. <i>Micromachines</i> , 2020 , 11,	3.3	2
48	One-Transistor Dynamic Random-Access Memory Based on Gate-All-Around Junction-Less Field-Effect Transistor with a Si/SiGe Heterostructure. <i>Electronics (Switzerland)</i> , 2020 , 9, 2134	2.6	2
47	Effects of Proton Irradiation on the Current Characteristics of SiN-Passivated AlGaN/GaN MIS-HEMTs Using a TMAH-Based Surface Pre-Treatment. <i>Micromachines</i> , 2021 , 12,	3.3	2
46	Microwave analysis of SiGe heterojunction double-gate tunneling field-effect transistor through its small-signal equivalent circuit. <i>International Journal of RF and Microwave Computer-Aided Engineering</i> , 2019 , 29, e21678	1.5	2
45	Design optimization of GaN diode with p-GaN multi-well structure for high-efficiency betavoltaic cell. <i>Nuclear Engineering and Technology</i> , 2021 , 53, 1284-1288	2.6	2
44	Design and optimization of GaN -based betavoltaic cell for enhanced output power density. <i>International Journal of Energy Research</i> , 2021 , 45, 799-806	4.5	2
43	Analysis of Electrical Characteristics of InAlGaN/GaN-Based High Electron Mobility Transistors with AlGaN Back Barriers. <i>Journal of Nanoscience and Nanotechnology</i> , 2019 , 19, 6008-6015	1.3	1
42	Design and analysis of logic inverter using antimonide-based compound semiconductor junctionless transistor. <i>Applied Physics A: Materials Science and Processing</i> , 2019 , 125, 1	2.6	1
41	Characteristics of temperature rise in variable inductor employing magnetorheological fluid driven by a high-frequency pulsed voltage source. <i>Journal of Applied Physics</i> , 2015 , 117, 17D508	2.5	1
40	Recessed-Gate GaN Metal-Insulator-Semiconductor High-Electron-Mobility Transistor Using a Dual Gate-Insulator Employing TiO ₂ /SiN. <i>Journal of Nanoscience and Nanotechnology</i> , 2020 , 20, 4678-4683	1.3	1
39	Electrical Performances of InN/GaN Tunneling Field-Effect Transistor. <i>Journal of Nanoscience and Nanotechnology</i> , 2017 , 17, 8355-8359	1.3	1
38	Design optimization of Si/Ge-based heterojunction arch-shaped gate-all-around (GAA) tunneling field-effect transistor (TFET) which applicable for future mobile communication systems 2016 ,		1
37	Dependence of device performances on fin dimensions in AlGaIn/GaN recessed-gate nanoscale FinFET 2014 ,		1
36	Fabrication and Characterization of GaN-based Light-emitting Diode (LED) with Triangle-type Structure. <i>Molecular Crystals and Liquid Crystals</i> , 2014 , 599, 163-169	0.5	1
35	Analysis on RF parameters of nanoscale tunneling field-effect transistor based on InAs/InGaAs/InP heterojunctions. <i>Journal of Nanoscience and Nanotechnology</i> , 2013 , 13, 8133-6	1.3	1
34	Rigorous Design and Analysis of Tunneling Field-Effect Transistor with Hetero-Gate-Dielectric and Tunneling-Boost n-Layer. <i>IEICE Transactions on Electronics</i> , 2013 , E96.C, 644-648	0.4	1
33	Compact modeling of silicon nanowire MOSFET for radio frequency applications. <i>Microwave and Optical Technology Letters</i> , 2011 , 53, 471-473	1.2	1
32	Extraction and modeling of gate electrode resistance in rf MOSFETs 2005 ,		1

31	Evaluation of Radio-Frequency Performance of Gate-All-Around Ge/GaAs Heterojunction Tunneling Field-Effect Transistor with Hetero-Gate-Dielectric by Mixed-Mode Simulation. <i>Journal of Electrical Engineering and Technology</i> , 2014 , 9, 2070-2078	1.4	1
30	Electrohydrodynamic Analysis of Dielectric Guide Flow Due to Surface Charge Density Effects in Breakdown Region. <i>Journal of Electrical Engineering and Technology</i> , 2015 , 10, 647-652	1.4	1
29	Improving of Sensitivity of Pbs Quantum Dot Based SWIR Photodetector Using P3HT. <i>Materials</i> , 2021 , 14,	3.5	1
28	Experimental and simulation study of power performance improvement of GaN PIN betavoltaic cell. <i>International Journal of Energy Research</i> , 2021 , 45, 17622-17630	4.5	1
27	Improved Negative Bias Stress Stability of Sol-Gel-Processed Li-Doped SnO ₂ Thin-Film Transistors. <i>Electronics (Switzerland)</i> , 2021 , 10, 1629	2.6	1
26	Polycrystalline-Silicon-MOSFET-Based Capacitorless DRAM With Grain Boundaries and Its Performances. <i>IEEE Access</i> , 2021 , 1-1	3.5	1
25	Analysis of tunneling field-effect transistor with germanium source junction using small-signal equivalent circuit. <i>Microwave and Optical Technology Letters</i> , 2018 , 60, 2922-2927	1.2	1
24	Flexible Sol-Gel-Processed YO RRAM Devices Obtained via UV/Ozone-Assisted Photochemical Annealing Process.. <i>Materials</i> , 2022 , 15,	3.5	1
23	Design Optimization of InGaAs/GaAsSb-Based -Type Gate-All-Around Arch-Shaped Tunneling Field-Effect Transistor. <i>Journal of Nanoscience and Nanotechnology</i> , 2019 , 19, 6762-6766	1.3	0
22	Design of Capacitorless DRAM Based on Polycrystalline Silicon Nanotube Structure. <i>IEEE Access</i> , 2021 , 9, 163675-163685	3.5	0
21	Numerical Design of Carrier Transporting Layer in Top-Gate InGaZnO Thin-Film Transistors for Controlling Potential Energy. <i>Journal of Nanoscience and Nanotechnology</i> , 2021 , 21, 3847-3852	1.3	0
20	Design of a Capacitorless Dynamic Random Access Memory Based on Ultra-Thin Polycrystalline Silicon Junctionless Field-Effect Transistor with Dual-Gate. <i>Journal of Nanoscience and Nanotechnology</i> , 2021 , 21, 4223-4229	1.3	0
19	Analysis of Grain Boundary Dependent Memory Characteristics in Poly-Si One-Transistor Dynamic Random-Access Memory. <i>Journal of Nanoscience and Nanotechnology</i> , 2021 , 21, 4216-4222	1.3	0
18	Design of a Capacitorless Dynamic Random Access Memory Based on Junctionless Dual-Gate Field-Effect Transistor with a Silicon-Germanium/Silicon Nanotube. <i>Journal of Nanoscience and Nanotechnology</i> , 2021 , 21, 4235-4242	1.3	0
17	Room-Temperature High-Detectivity Flexible Near-Infrared Photodetectors with Chalcogenide Silver Telluride Nanoparticles.. <i>ACS Omega</i> , 2022 , 7, 10262-10267	3.9	0
16	Analysis of Logic Inverter Based on Polycrystalline Silicon with Single Grain Boundary. <i>Journal of Nanoscience and Nanotechnology</i> , 2020 , 20, 6616-6621	1.3	
15	Design Optimization of Ge/GaAs-Based Heterojunction Gate-All-Around (GAA) Arch-Shaped Tunneling Field-Effect Transistor (A-TFET). <i>Journal of Nanoscience and Nanotechnology</i> , 2018 , 18, 6602-6605	1.3	0.5
14	Simulation for Electrical Performances of the Capacitorless Dynamic Random Access Memory Based on Junctionless FinFETs. <i>Journal of Nanoscience and Nanotechnology</i> , 2019 , 19, 6755-6761	1.3	

13	Highly enhanced charge injection and bulk transport in organic gap-type diodes via one-pot treatment process: experiment and simulation. <i>Micro and Nano Letters</i> , 2014 , 9, 887-890	0.9
12	Effects of electrical stress on mid-gap interface trap density and capture cross sections in n-MOSFETs characterized by pulsed interface probing measurements. <i>Microelectronics Reliability</i> , 2004 , 44, 47-51	1.2
11	Analysis of CMOS Logic Inverter Based on Gate-All-Around Field-Effect Transistors with the Strained-Silicon Layer for Improving the Switching Performances. <i>Journal of Nanoscience and Nanotechnology</i> , 2020 , 20, 6632-6637	1.3
10	Design and Analysis of Metal-Oxide-Semiconductor Field-Effect Transistor-Based Capacitorless One-Transistor Embedded Dynamic Random-Access Memory with Double-Polysilicon Layer Using Grain Boundary for Hole Storage. <i>Journal of Nanoscience and Nanotechnology</i> , 2020 , 20, 6596-6602	1.3
9	Design Optimization and Analysis of InGaAs-Based Gate-All-Around (GAA) Junctionless Field-Effect Transistor (JLFET). <i>Journal of Nanoscience and Nanotechnology</i> , 2017 , 17, 8350-8354	1.3
8	Charge Based Current-Voltage Model for the Silicon on Insulator Junctionless Field-Effect Transistor. <i>Journal of Nanoscience and Nanotechnology</i> , 2020 , 20, 4920-4925	1.3
7	Theoretical Analysis of Prospects of Organic Photovoltaics as a Multi-Functional Solar Cell and Laser Power Converter for Wireless Power Transfer. <i>Journal of Nanoscience and Nanotechnology</i> , 2020 , 20, 4878-4883	1.3
6	DC and RF Analysis of Geometrical Parameter Changes in the Current Aperture Vertical Electron Transistor. <i>Journal of Electrical Engineering and Technology</i> , 2016 , 11, 1763-1768	1.4
5	Effect of Electric Fringe-Field on Low-Power and Radio-Frequency Performances of Sub-10 nm Junctionless Transistors with Hetero-Dielectric Spacer Structure. <i>Journal of Nanoscience and Nanotechnology</i> , 2017 , 17, 7140-7144	1.3
4	Extraction of T-Type Substrate Resistance Components for Radio-Frequency Metal-Oxide-Semiconductor Field-Effect Transistors Based on Two-Port-Parameter Measurement. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 111201	1.4
3	Simulation of One-Transistor Dynamic Random-Access Memory Based on Symmetric Double-Gate Si Junctionless Transistor. <i>Journal of Nanoscience and Nanotechnology</i> , 2018 , 18, 6593-6597	1.3
2	The Effect of Grain Boundary on Electrical Characteristics in the Source and Drain Regions of Polycrystalline Silicon Based in One Transistor Dynamic Random Access Memory. <i>Journal of Nanoscience and Nanotechnology</i> , 2021 , 21, 4258-4267	1.3
1	Design and Analysis of DC/DC Boost Converter Using Vertical GaN Power Device. <i>Journal of Nanoscience and Nanotechnology</i> , 2021 , 21, 4320-4324	1.3